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1. Global joint venture starts operations as WeEn Semiconductors

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In this document where the previous NXP references remain, please use the new links as shown below.

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Product data sheet

1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220-F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quie	ck reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{RRM}	repetitive peak reverse voltage			-	-	600	V	
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 61 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	10	A	
Static characte	eristics							
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.3	2	V	
Dynamic characteristics								
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	12	18	ns	





5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	К — А
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113A)	

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BYC10X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack"	SOD113A

7. Marking

Table 4. Marking codes	
Type number	Marking code
BYC10X-600P	BYC10X-600P

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mir	n Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 61 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t_p = 25 µs; T_h \leq 61 °C; square-wave pulse	-	20	A
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BYC10X-600P

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Symbol	Parameter	Conditions	Min	Max	Unit
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	150	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	165	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

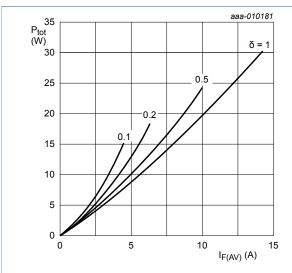
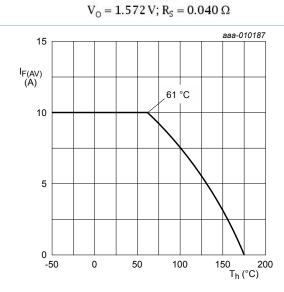
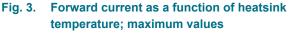


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$





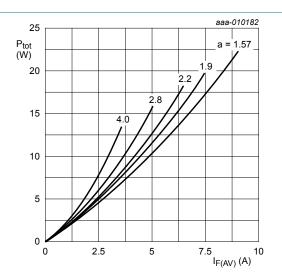
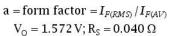


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



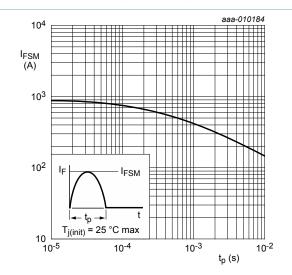
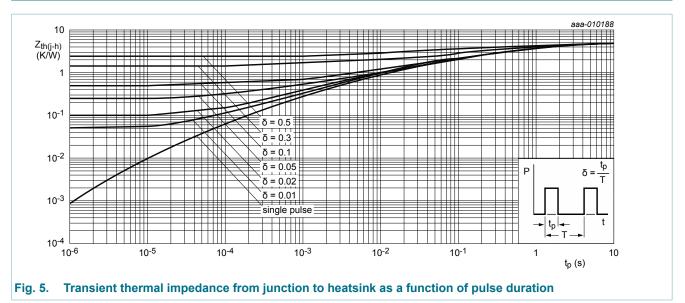


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Hyperfast power diode

9. Thermal characteristics

Table 6. T	hermal characteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	4.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



10. Isolation characteristics

	Min		Max	Unit
-	-	Тур -	2500	V
		10	_	pF
		-	- 10	- 10 -

11. Characteristics

Table 8. C	haracteristics						
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
Static characteristics							
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.2	V	
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.3	2	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	0.8	mA
Dynamic c	haracteristics	· · · · ·	l.			,
Q _r re	recovered charge	I _F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	26	-	nC
		I_F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ µs; T _j = 125 °C; <u>Fig. 7</u>	-	83	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	12	18	ns
		I_F = 10 A; V_R = 400 V; dI_F/dt = 500 A/ µs; T_j = 25 °C; <u>Fig. 7</u>	-	19	-	ns
		I_F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ µs; T _j = 25 °C; <u>Fig. 7</u>	-	26	-	ns
		I_F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ µs; T _j = 125 °C; <u>Fig. 7</u>	-	34	-	ns
I _{RM}	peak reverse recovery current	I_F = 10 A; V _R = 200 V; dI _F /dt = 200 A/ µs; T _j = 25 °C; <u>Fig. 7</u>	-	2	-	A
		I_F = 10 A; V_R = 200 V; dI_F/dt = 200 A/ µs; T_j = 125 °C; <u>Fig. 7</u>	-	4.8	-	A

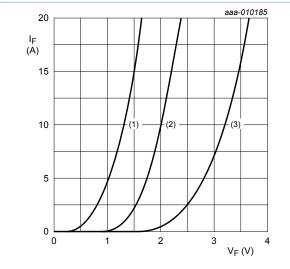
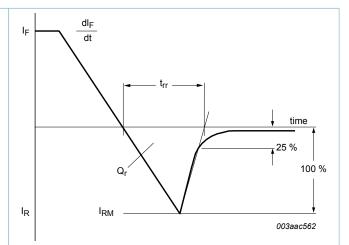


Fig. 6. Forward current as a function of forward voltage

(1) T_j = 150 °C; typical values;
 (2) T_j = 150 °C; maximum values;
 (3) T_j = 25 °C; maximum values;
 V_O = 1.572 V; R_S = 0.040 Ω





Hyperfast power diode

12. Package outline

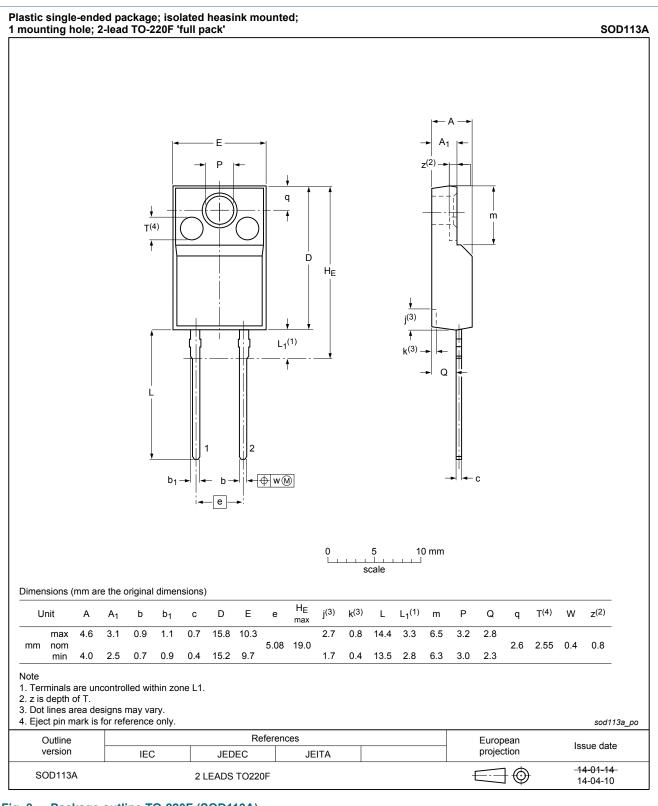


Fig. 8. Package outline TO-220F (SOD113A) BYC10X-600P All informati

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Hyperfast power diode

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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